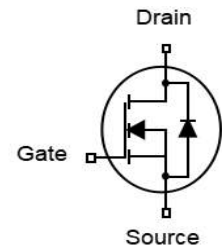


Features

- N-Channel
- Low FOM $R_{DS(on)} \times Q_{gd}$
- Ultra-low on-resistance
- Halogen-free
- RoHS compliant
- 100% EAS Tested

V_{DS}	150	V
$R_{DS(on),TYP@ V_{GS}=10V}$	5.6	m Ω
I_D	140	A

TO-247



Part ID	Package Type	Marking	Packing
ZTG060N15T	TO-247	ZTG060N15T	600pcs/Tape

Absolute Maximum Ratings $T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Rating	Unit	
Common Ratings ($T_c=25^\circ\text{C}$ Unless Otherwise Noted)				
V_{GS}	Gate-Source Voltage	± 20	V	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	150	V	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$	
I_{DM}	Drain Current-Continuous@ Current-Pulsed (Note 2)	$T_c = 25^\circ\text{C}$ 560	A	
Mounted on Large Heat Sink				
I_D	Drain Current-Continuous (Note 1)	$T_c = 25^\circ\text{C}$	140	A
		$T_c = 100^\circ\text{C}$	100	A
P_D	Maximum Power Dissipation	200	W	
$R_{\omega JC}$	Thermal Resistance-Junction to Case	0.47	$^\circ\text{C/W}$	
Drain-Source Avalanche Ratings				
EAS	Avalanche Energy, Single Pulsed (Note 3)	625	mJ	

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J=25°C (unless otherwise stated)						
V _(BR) DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	150	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =150V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2.0	3.0	4.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =20A	--	5.6	6.5	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =75V, V _{GS} =0V, f=1MHz	--	5926	--	pF
C _{oss}	Output Capacitance		--	544	--	pF
C _{rss}	Reverse Transfer Capacitance		--	23	--	pF
R _g	Gate Resistance f=1MHz	f=1MHz	--	2.2	--	Ω
Q _g	Total Gate Charge	V _{DS} =75V, I _D =20A, V _{GS} =10V	--	83	--	nC
Q _{gs}	Gate-Source Charge		--	24.8	--	nC
Q _{gd}	Gate-Drain Charge		--	16.9	--	nC
Switching Characteristics						
T _{d(on)}	Turn-on Delay Time	V _{DD} =75V, R _L =3.75Ω, R _G =6Ω, V _{GS} =10V	--	32	--	ns
T _r	Turn-on Rise Time		--	49	--	ns
T _{d(off)}	Turn-Off Delay Time		--	80	--	ns
T _f	Turn-Off Fall Time		--	46	--	ns
Source- Drain Diode Characteristics @ T_J = 25°C (unless otherwise stated)						
I _{SD}	Source-Drain Current (Body Diode)		--	--	140	A
V _{SD}	Forward on voltage	I _S =20A, V _{GS} =0V	--	--	1.2	V
T _{rr}	Reverse Recovery Time	T _J =25°C, I _D =15A, di/dt=100A/μs	--	90	--	ns
Q _{rr}	Reverse Recovery Charge		--	360	--	nC

Notes:

1. The max drain current rating is package limited
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. L = 0.5 mH, V_{DD} = 75V, I_{AS} = 50 A, R_G = 25 Ω, Starting T_J = 25 °C

Electrical Characteristics Diagrams

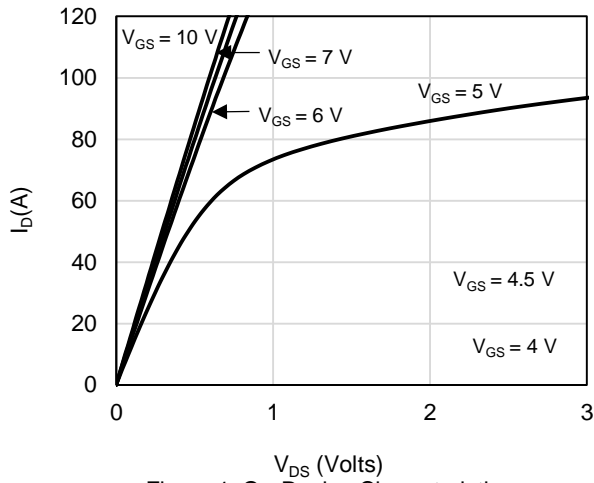


Figure 1: On-Region Characteristics

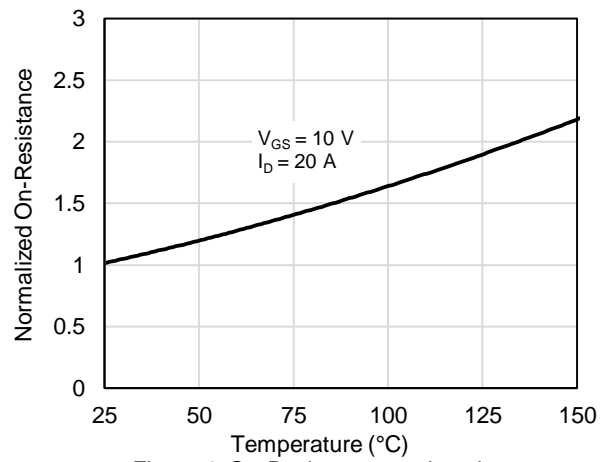


Figure 4: On-Resistance vs. Junction Temperature

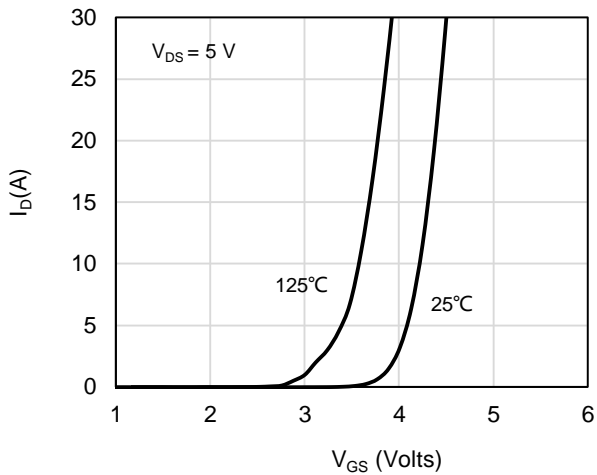


Figure 2: Transfer Characteristics

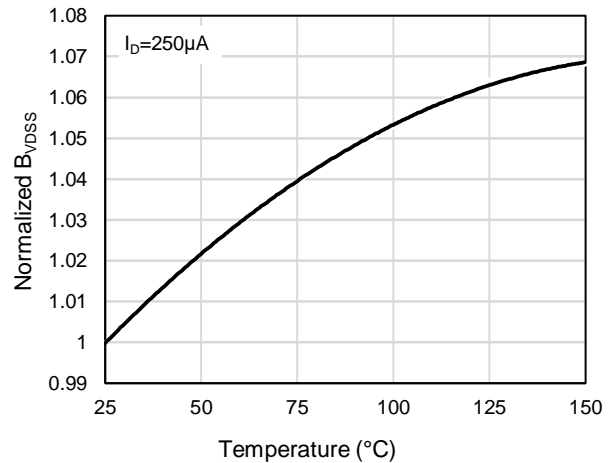


Figure 5: Breakdown Voltage vs. Junction Temperature

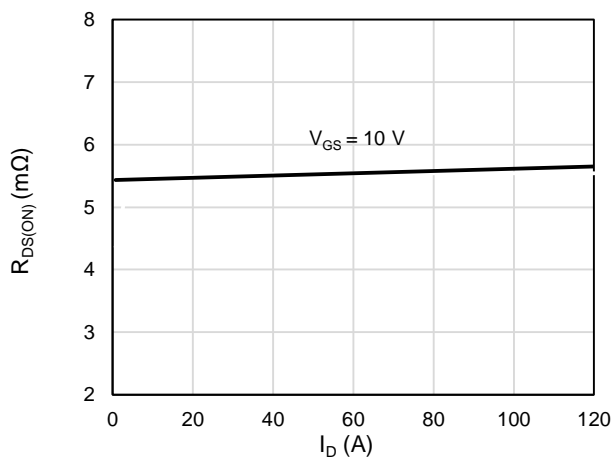


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

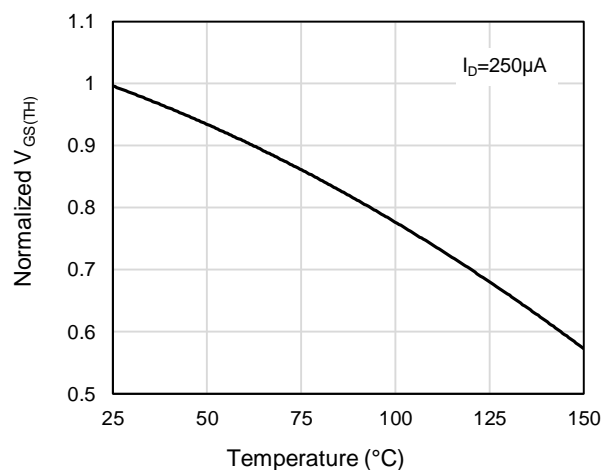


Figure 6: Threshold Voltage vs. Junction Temperature

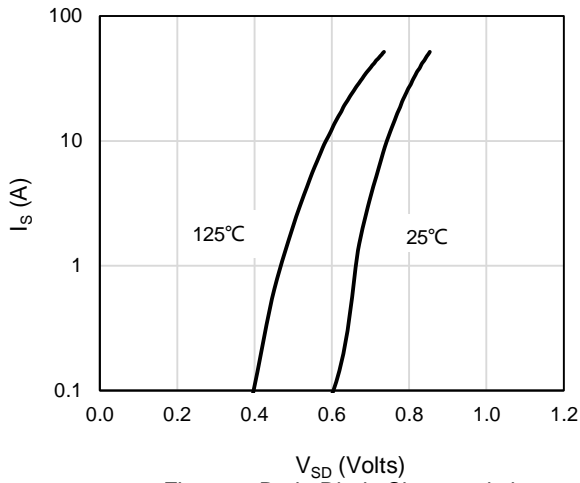


Figure 7: Body-Diode Characteristics

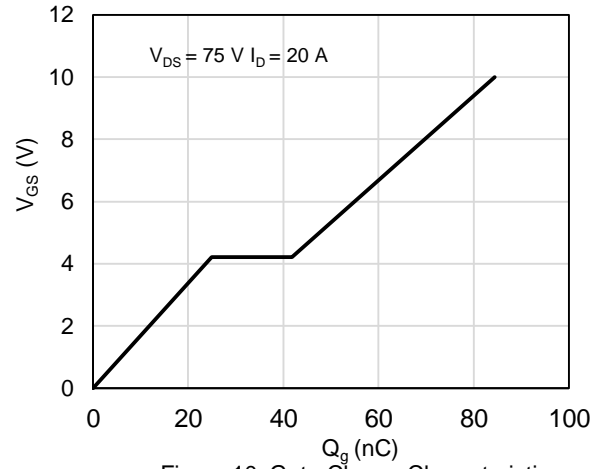


Figure 10: Gate-Charge Characteristics

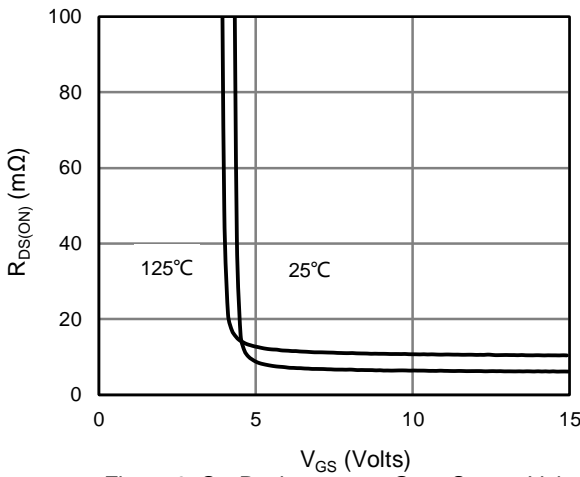


Figure 8: On-Resistance vs. Gate-Source Voltage

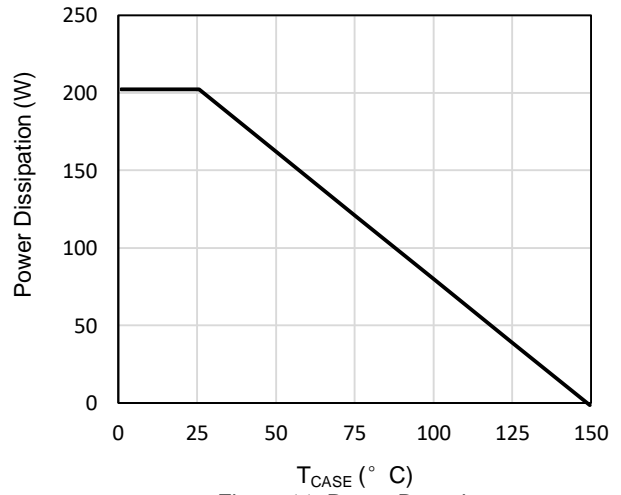


Figure 11: Power De-rating

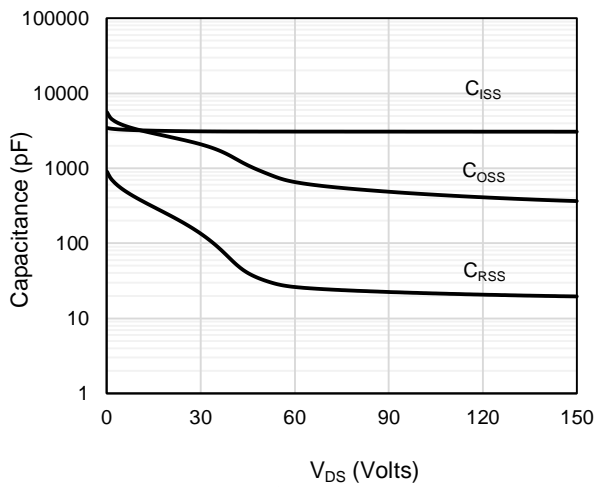


Figure 9: Capacitance Characteristics

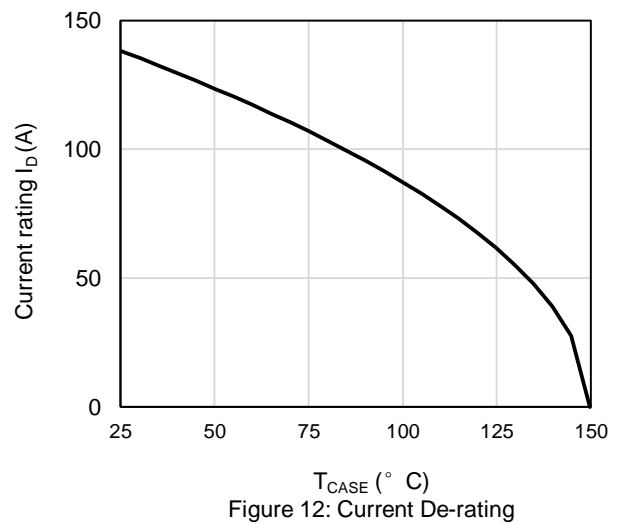


Figure 12: Current De-rating

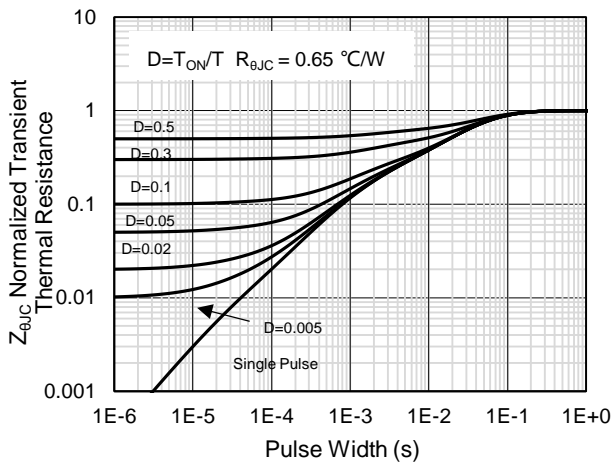


Figure 13: Normalized Maximum Transient Thermal Impedance

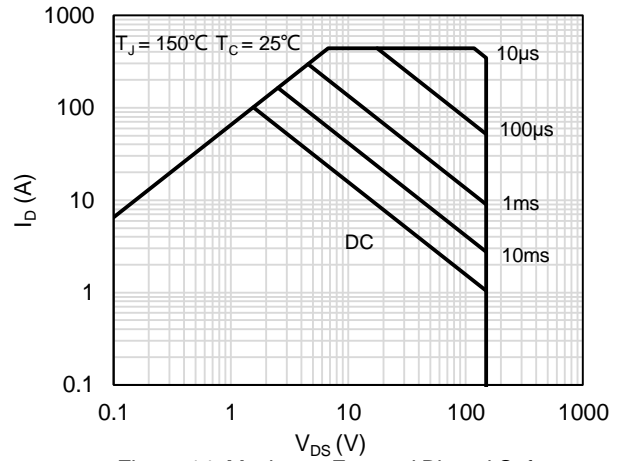
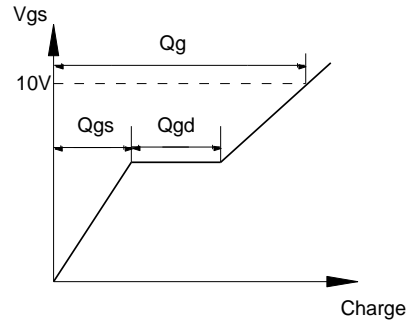
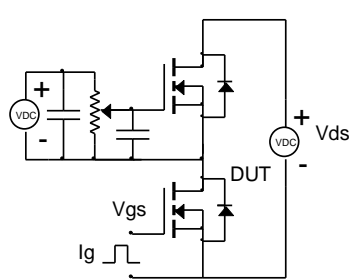


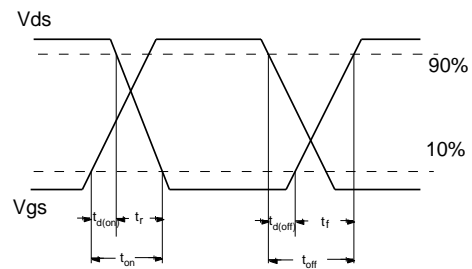
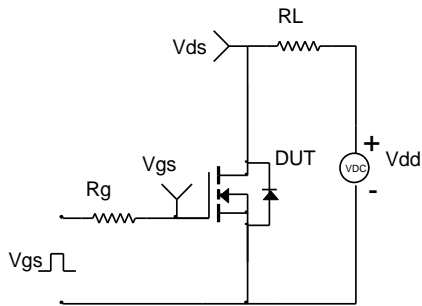
Figure 14: Maximum Forward Biased Safe Operating Area

Test Circuit and Waveform

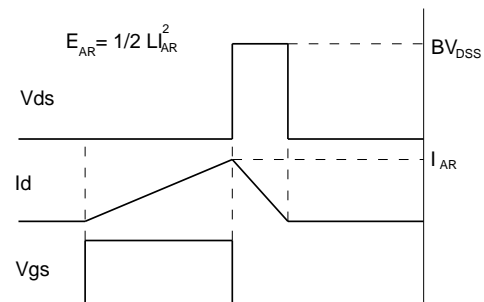
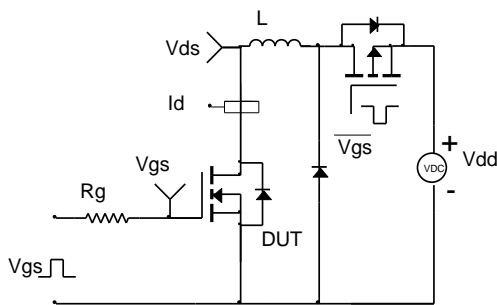
Gate Charge Test Circuit & Waveform



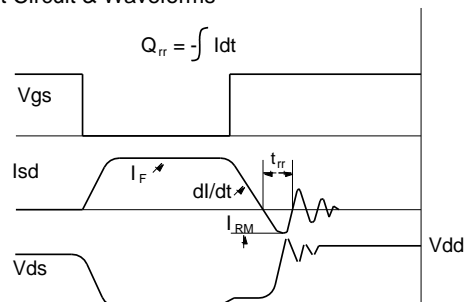
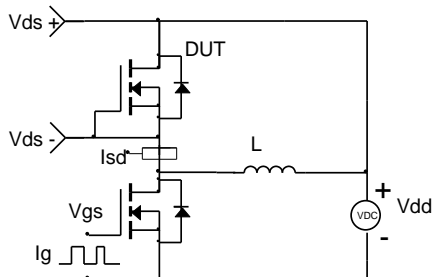
Resistive Switching Test Circuit & Waveforms



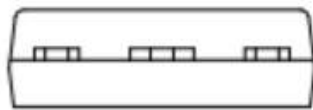
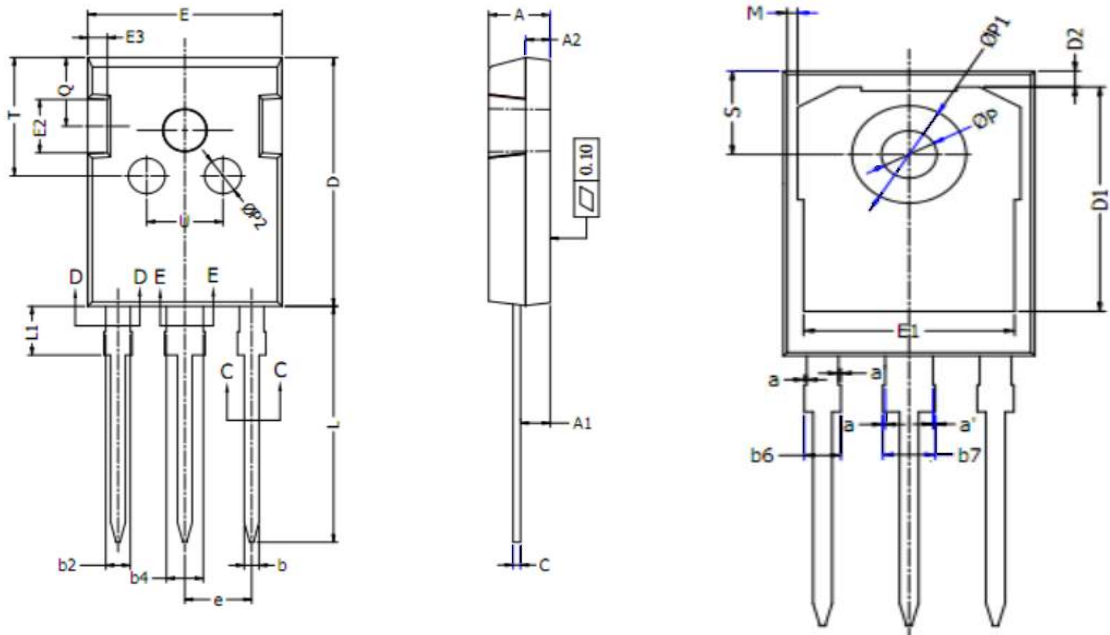
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



TO-247 Package Information



SYMBOL	MIN	NOM	MAX
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
a	0	---	0.15
a'	0	---	0.15
b	1.16	---	1.26
b1	1.15	1.2	1.22
b2	1.96	---	2.06
b3	1.95	2.00	2.02
b4	2.96	---	3.06
b5	2.96	3.00	3.02
b6	---	---	2.25
b7	---	---	3.25
c	0.59	---	0.66
c1	0.58	0.60	0.62
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.17	1.35
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.40	4.50	4.60
E3	1.50	1.60	1.70
e	5.436 BSC		
L	19.80	19.92	20.10
L1	---	---	4.30
M	0.35	---	0.95
P	3.40	3.50	3.60
P1	7.00	---	7.40
P2	2.40	2.50	2.60
Q	5.60	---	6.00
S	6.05	6.15	6.25
T	9.80	---	10.20
U	6.00	---	6.40

Customer Service

Sales and Service:

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